

Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I _D	7.5 4.7	А
Maximum Body Diode Forward Current (Note 6)	Is	1.5	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	30	Α	
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	30	Α	
Avalanche Current	L = 0.1mH	I _{AS}	4.7	А
Avalanche Energy	L = 0.1mH	E _{AS}	1.1	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _C = +25°C	PD	18.7	W
Total Power Dissipation (Note 5)	$T_{C} = +100^{\circ}C$	T PD	7.5	
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	92	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R ₀ JC	6.7	C/VV	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

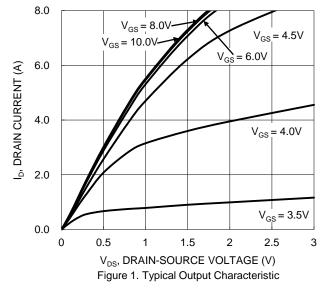
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	1.5	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	В	_	179	220	mΩ	$V_{GS} = 10V, I_D = 2A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	_	228	250	mΩ	$V_{GS} = 4.5V, I_D = 1A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	$V_{GS} = 0V$, $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	384	_		V _{DS} = 25V, f = 1MHz, V _{GS} = 0V	
Output Capacitance	Coss	_	23	_	pF		
Reverse Transfer Capacitance	Crss	_	17	_		VGS = 0V	
Gate Resistance	R _G	_	2.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	3.7	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	6.7	_	nC	\/ F0\/ 4.6A	
Gate-Source Charge	Qgs	_	1.3	_	i iic	$V_{DD} = 50V, I_D = 1.6A$	
Gate-Drain Charge	Q_{gd}	_	2	_			
Turn-On Delay Time	t _{D(ON)}	_	6.2	_		$V_{DD} = 50V, V_{GS} = 4.5V,$ $R_G = 6.8\Omega, I_D = 1.0A$	
Turn-On Rise Time	t _R	_	8.7	_			
Turn-Off Delay Time	t _{D(OFF)}	_	7.4	_	ns		
Turn-Off Fall Time	t _F	_	4.2	_			
Body Diode Reverse Recovery Time	t _{RR}	_	20	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	11	_	nC	-I _S = 1.1A, dl/dt = 100A/μs	

Notes:

- 5. Device mounted on infinite heatsink.
 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 7. Guaranteed by design. Not subject to production testing.
 8. Short duration pulse test used to minimize self-heating effect.





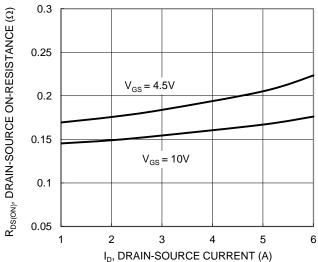


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

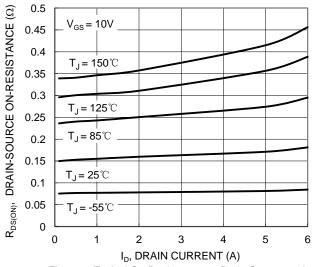
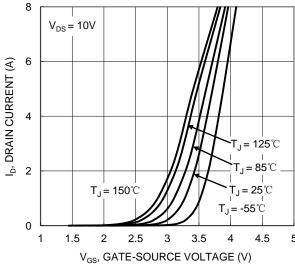


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

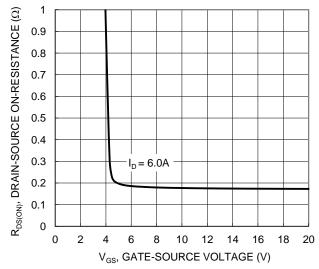


Figure 4. Typical Transfer Characteristic

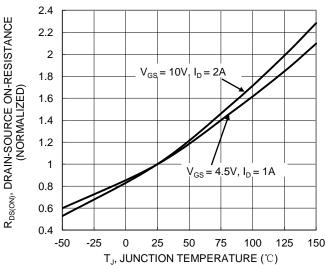


Figure 6. On-Resistance Variation with Junction Temperature



DMN10H220LK3

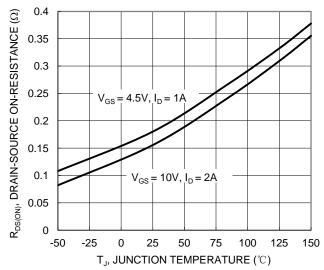


Figure 7. On-Resistance Variation with Junction Temperature

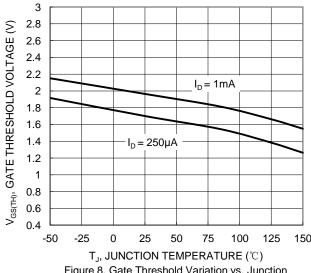


Figure 8. Gate Threshold Variation vs. Junction Temperature

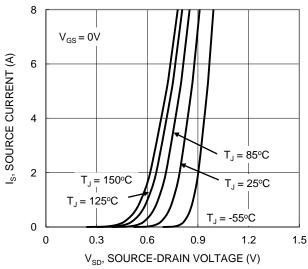


Figure 9. Diode Forward Voltage vs. Current

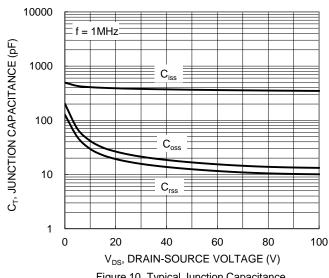
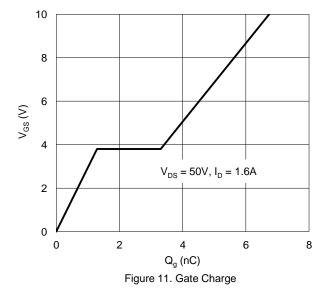
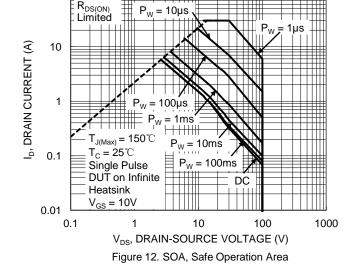


Figure 10. Typical Junction Capacitance





100



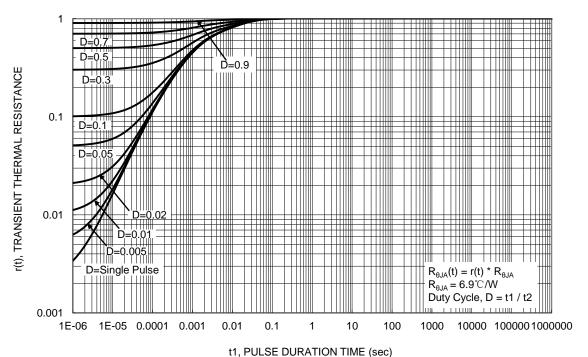


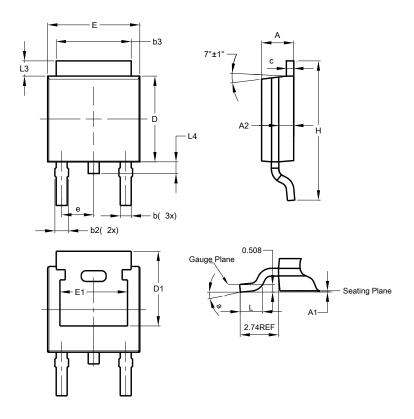
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

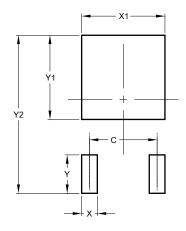


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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